

## SOT-23 Plastic-Encapsulate Transistors



SOT-23

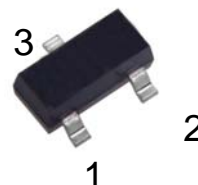


## 2SC1815 TRANSISTOR (NPN)

## FEATURES

Power dissipation

MARKING : HF



- 1.Base (B)  
2. Emitter (E)  
3.Collector (C)

MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	150	mA
$P_C$	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C}/\text{W}$
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

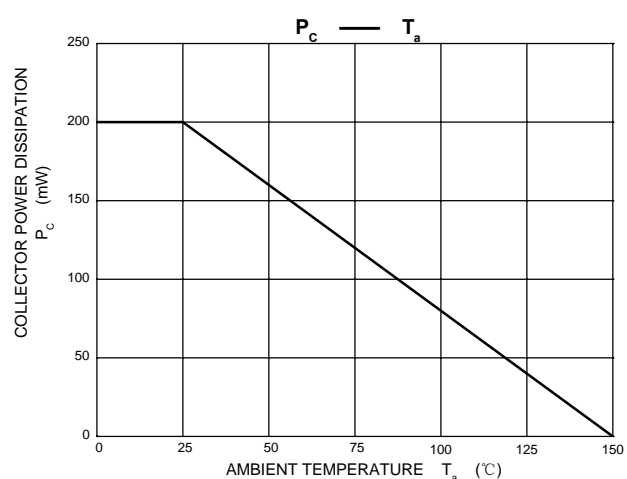
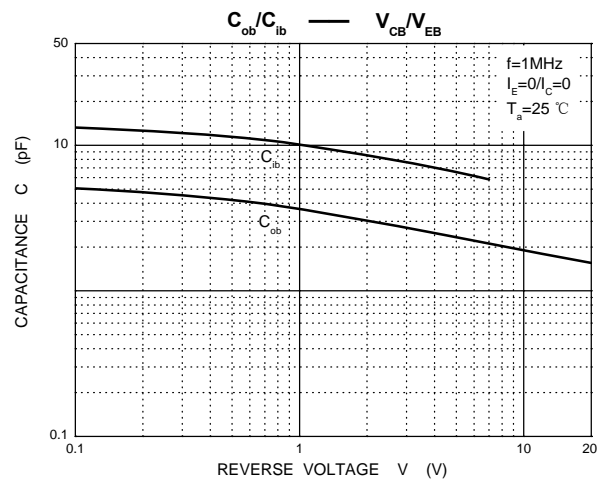
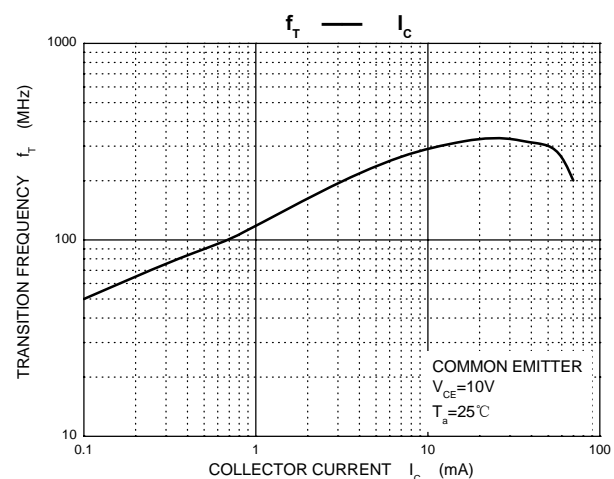
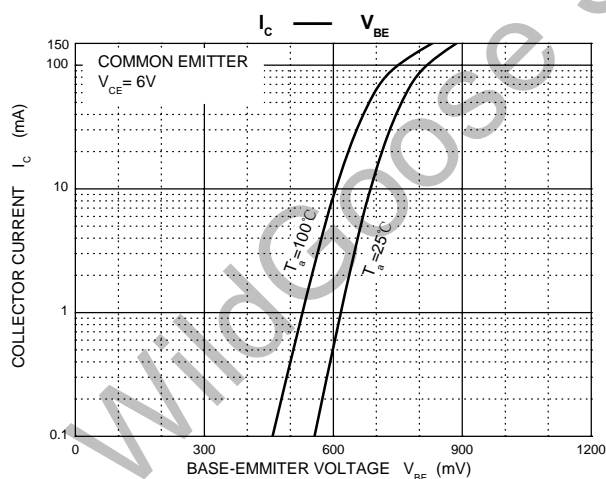
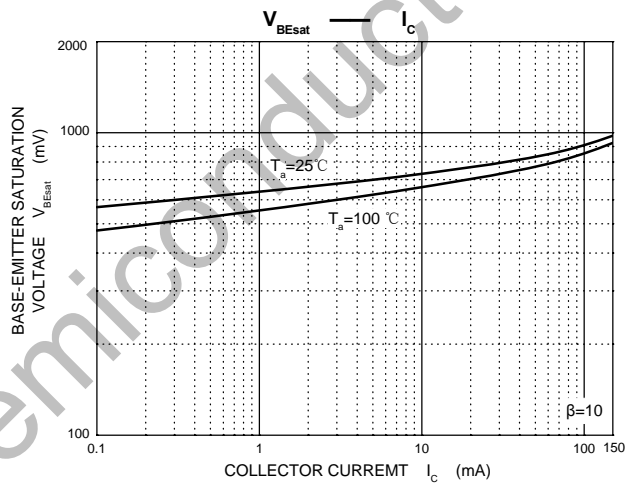
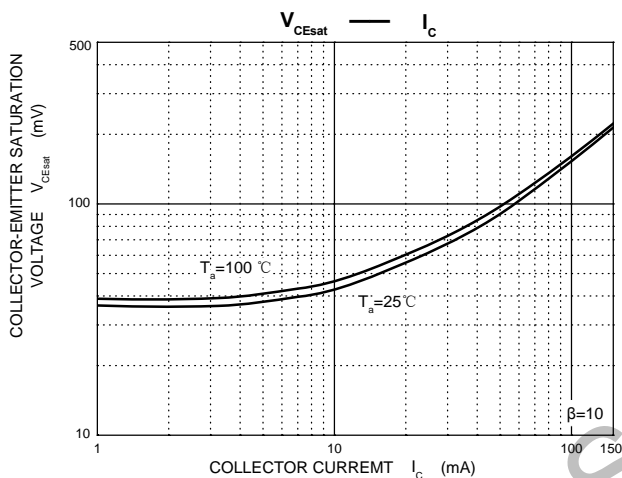
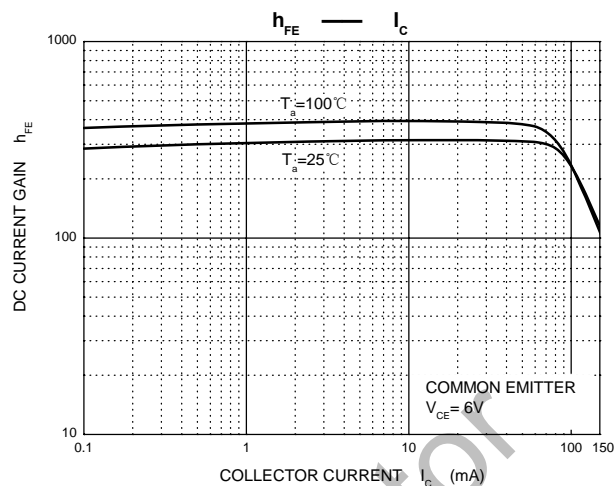
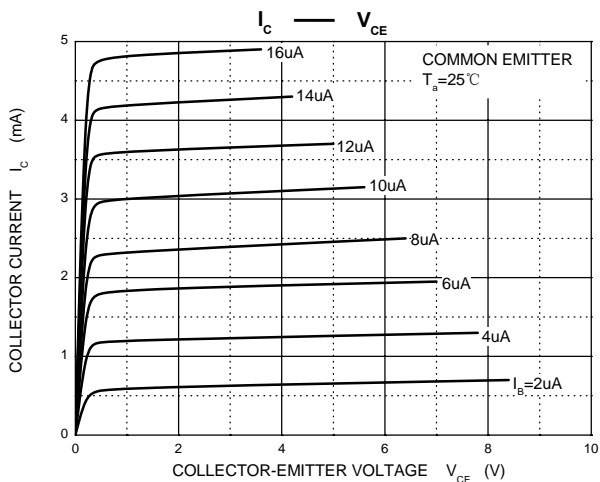
ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=2\text{mA}$	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_C=1\text{mA}, f=30\text{MHz}$	80			MHz

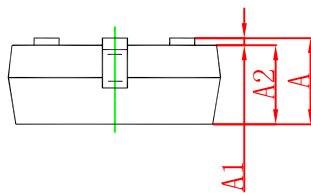
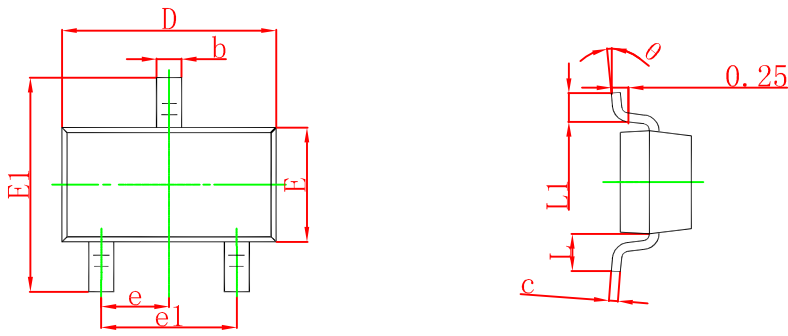
CLASSIFICATION OF  $h_{FE}$ 

Rank	L	H
Range	120-240	200-400

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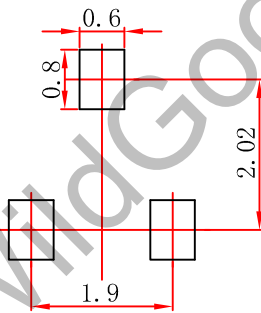


SOT-23 Plastic-Encapsulate Transistors



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance: ± 0.05mm.
  3. The pad layout is for reference purposes only.

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